

ABSTRACT

A semiconductor device is disclosed. The semiconductor device may include a first interlayer insulating layer on a semiconductor substrate, first conductive patterns penetrating the first interlayer insulating layer, a second interlayer insulating layer on the first interlayer insulating layer, second conductive patterns provided in the second interlayer insulating layer and coupled to the first conductive patterns, and separation insulating patterns provided in the second interlayer insulating layer between the second conductive patterns. A portion of the second interlayer insulating layer may be between side surfaces of the separation insulating patterns and side surfaces of the second conductive patterns.

FIG. 2B